PROGRESS IN CRYSTAL GROWTH AND CHARACTERIZATION OF MATERIALS

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CONTENTS

Introduction i

Optical and x-ray topographical investigations of synthetically grown quartz crystals with induced growth striations 1
H. BERNHARDT, J. HÄRTWIG and V. LERCHE

Structural transformation in silicon by pulse heating 53
L. N. ALEKSANDROV

Design and modeling of chemical vapor deposition reactors 111
W. L. HOLSTEIN

Physico-chemical investigations on crystal growth of oxide superconductors 213
C. CHANGKANG

Crystal chemistry and its significance on the growth of technological materials: Part I; silicates, phosphates and their analogues 269
K. BYRAPPA and D. Yu. PUSHCHAROVSKY

Crystal chemistry and its significance on the growth of technological materials: Part II; octahedrally coordinated compounds 361
K. BYRAPPA and D. Yu. PUSHCHAROVSKY